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Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild_questions@onsemi.com.

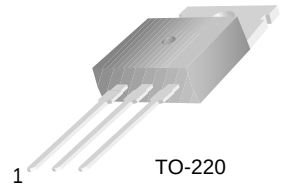
FAIRCHILD SEMICONDUCTOR®

July 2008

FJP3307D
High Voltage Fast Switching NPN Power Transistor

Features

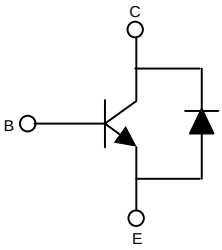
- Built-in Diode between Collector and Emitter
- Suitable for Electronic Ballast and Switch Mode Power Supplies



TO-220

1.Base 2.Collector 3.Emitter

Internal Schematic Diagram



Absolute Maximum Ratings

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	700	V
V_{CEO}	Collector-Emitter Voltage	400	V
V_{EBO}	Emitter-Base Voltage	9	V
I_C	Collector Current (DC)	8	A
I_{CP}	* Collector Current (Pulse)	16	A
I_B	Base Current (DC)	4	A
P_C	Collector Dissipation (T_C = 25°C)	80	W
T_J	Junction Temperature	150	°C
T_{STG}	Storage Temperature	-55 ~ 150	°C

* Pulse Test: PW = 300ms, Duty Cycle = 2% Pulsed

Electrical Characteristics T_C = 25°C unless otherwise noted

Symbol	Parameter	Conditions	Min.	Typ.	Max	Units
BV_{CBO}	Collector-Base Breakdown Voltage	I_C = 500μA, I_E = 0	700			V
BV_{CEO}	Collector-Emitter Breakdown Voltage	I_C = 5mA, I_B = 0	400			V
BV_{EBO}	Emitter-Base Breakdown Voltage	I_E = 500μA, I_C = 0	9			V
I_{EBO}	Emitter Cut-off Current	V_{EB} = 9V, I_C = 0			1	mA
h_{FE1} h_{FE2}	DC Current Gain	V_{CE} = 5V, I_C = 2A V_{CE} = 5V, I_C = 5A	8 5		40 30	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C = 2A, I_B = 0.4A			1	V
		I_C = 5A, I_B = 1A			2	V
		I_C = 8A, I_B = 2A			3	V

Symbol	Parameter	Conditions	Min.	Typ.	Max	Units
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C = 2A, I_B = 0.4A			1.2	V
		I_C = 5A, I_B = 1A			1.6	V
V_F	Diode Forward Voltage	I_C = 3A			2.5	V
C_{ob}	Output Capatitance	V_{CB} = 10V, I_E = 0, f = 1MHz		60		pF
t_{STG}	Storage Time	V_{CC} = 125V, I_C = 5A I_{B1} = -I_{B2} = 1A, R_L = 50Ω			3	μs
t_F	Fall Time				0.7	μs
t_{STG}	Storage Time	V_{CC} = 30V, I_C = 5A, L=200μH I_{B1}=1A, R_{BB} = 0Ω, $V_{BE(OFF)}$= -5V V_{CLAMP} = 250V			2.3	μs
t_F	Fall Time				150	ns

* Pulse test: PW = 300μs, Duty cycl e= 2%

h_{FE} Classification

Classification	H1	H2
h_{FE1}	15 ~ 28	26 ~ 39

Typical Characteristics

Figure 1. Static Characterstic

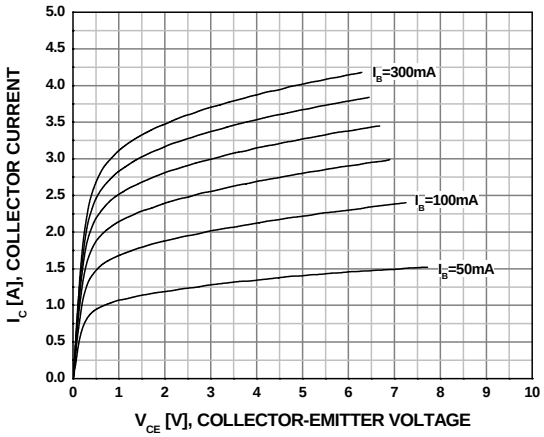


Figure 2. DC Current Gain (H1 Grade)

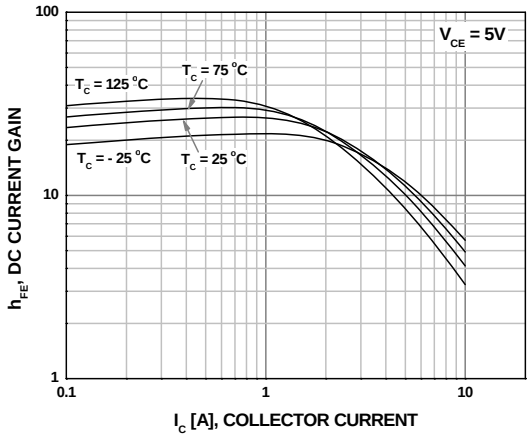


Figure 3. DC Current Gain (H2 Grade)

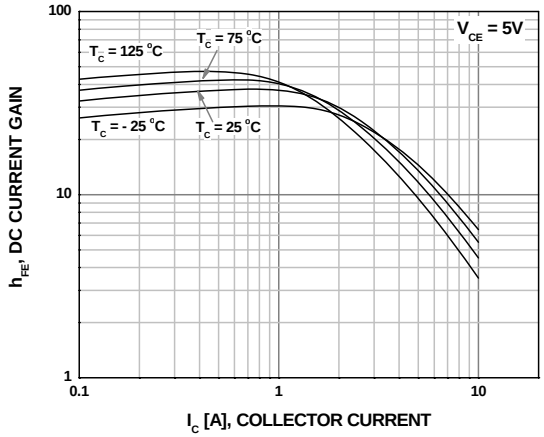


Figure 4. Collector-Emitter Saturation Voltage

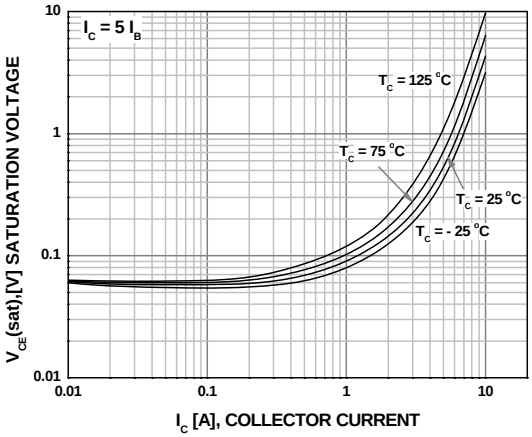


Figure 5. Base-Emitter Saturation Voltage

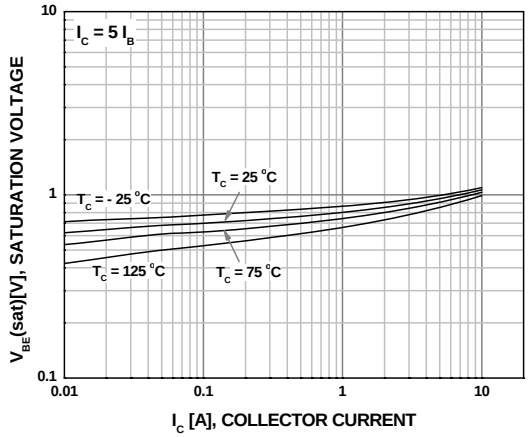
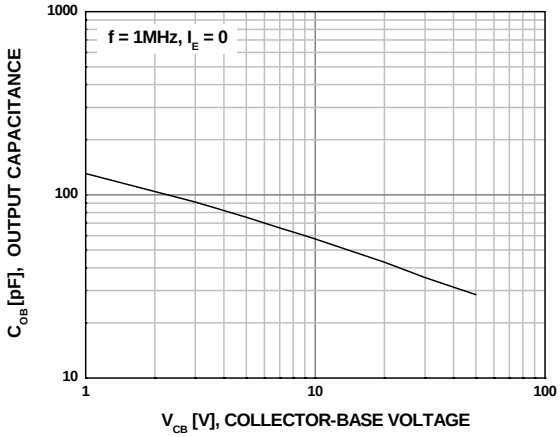


Figure 6. Output Capacitance



Typical Characteristics (Continued)

Figure 7. Power Derating

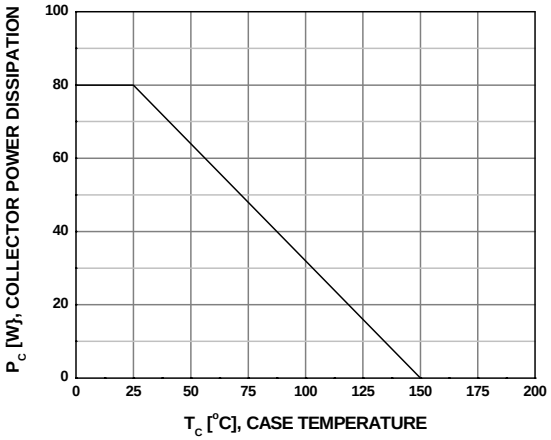


Figure 8. Reverse Biased Safe Operating Area

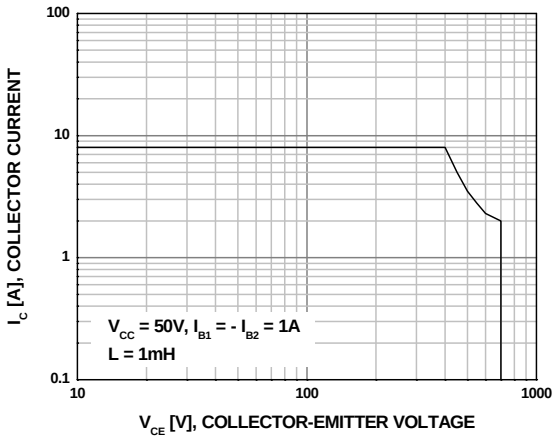
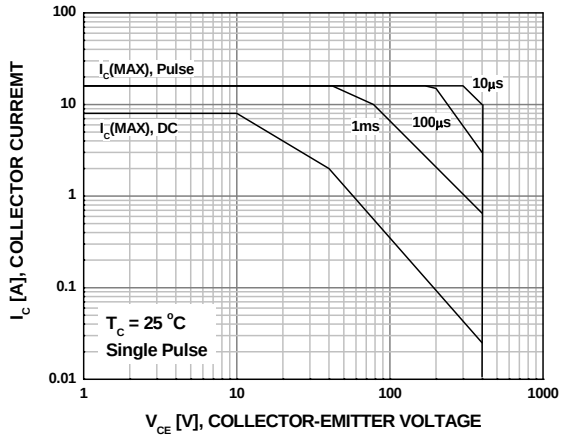
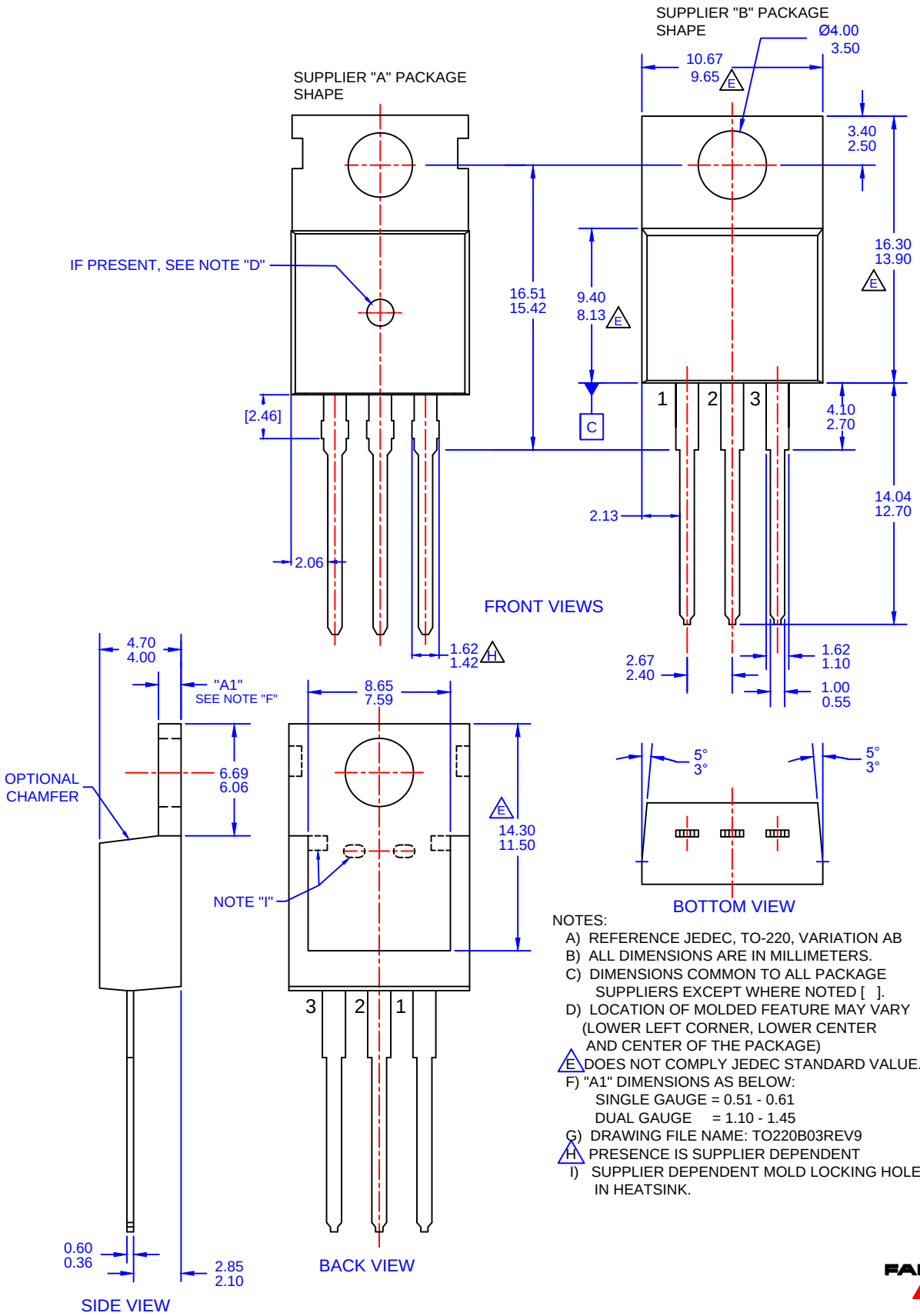


Figure 9. Forward Biased Safe Operating Area





NOTES:

A) REFERENCE JEDEC, TO-220, VARIATION AB
B) ALL DIMENSIONS ARE IN MILLIMETERS.
C) DIMENSIONS COMMON TO ALL PACKAGE SUPPLIERS EXCEPT WHERE NOTED [ ].
D) LOCATION OF MOLDED FEATURE MAY VARY (LOWER LEFT CORNER, LOWER CENTER AND CENTER OF THE PACKAGE)
E DOES NOT COMPLY JEDEC STANDARD VALUE.
F) "A1" DIMENSIONS AS BELOW:
SINGLE GAUGE = 0.51 - 0.61
DUAL GAUGE = 1.10 - 1.45
G) DRAWING FILE NAME: TO220B03REV9
H PRESENCE IS SUPPLIER DEPENDENT
I) SUPPLIER DEPENDENT MOLD LOCKING HOLES IN HEATSINK.

FAIRCHILD

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